

CHARACTERISATION OF BALLISTIC CARBON NANOTUBE
FIELD-EFFECT TRANSISTOR

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To my beloved parents and wife

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ABSTRACT

Scaling process of silicon transistor, particularly MOSFET, in the past decades had increased the performance of silicon transistor with reduction of its size. However, the scaling process will eventually reaches its limit and by that time a new group of devices are expected to replace MOSFET in digital applications. This group of devices, known as nanoelectronic devices, is expected to offer better device geometry in nanometre scale with superior performance. Carbon nanotube field-effect transistor (CNFET), one of nanoelectronic devices, is a transistor with its channel is made of carbon nanotube and it is designed to provide the solution for scaling process and the possibility of coexistence with current silicon technology. The purpose of this project is to study the behaviour of CNFET and the main focus is on the simulation of its current-voltage (I-V) characteristic. The simulation study is carried out using MATLAB program and the result obtained is used to compare the device performance with MOSFET. Further analysis is also made to see the effect of oxide thickness and carbon nanotube diameter on the device performance, in particular the drain current. From the simulation study, it is concluded that the performance of CNFET has no significant advantage over MOSFET and its performance is also affected by both nanotube diameter and oxide thickness.

ABSTRAK

Proses penskalaan terhadap transistor silikon, terutamanya MOSFET, selama beberapa dekad yang lalu telah berjaya memperbaiki pencapaian peranti ini serta mampu mengurangkan saiz peranti ini. Namun, proses ini akan tiba di had keupayaannya dan pada masa itu beberapa peranti baru akan menggantikan MOSFET dalam aplikasi digital. Kumpulan peranti ini, yang dikenali sebagai peranti elektronik-nano, dijangka akan memberikan bentuk peranti yang lebih baik dalam skala nanometer dan juga pencapaian yang mengagumkan. Transistor tiub-nano karbon (CNFET), salah satu daripada peranti elektronik-nano, merupakan transistor yang mempunyai saluran yang diperbuat daripada tiub-nano karbon dan ianya direkabentuk untuk memberikan penyelesaian terhadap masalah penskalaan dan berkemungkinan untuk diintegrasikan bersama teknologi silikon. Tujuan projek ini adalah untuk mengkaji sifat peranti ini dan fokus utama diberikan kepada simulasi terhadap sifat arus-voltan (I-V) peranti ini. Kajian simulasi ini dibuat menggunakan program MATLAB dan hasil keputusan yang dicapai akan digunakan untuk membandingkan pencapaian peranti ini dengan MOSFET. Analisis selanjutnya dilakukan untuk melihat kesan diameter tiub-nano karbon dan ketebalan oksida terhadap pencapaian peranti ini, atau lebih tepat lagi terhadap arus drain. Hasil keputusan yang dicapai daripada kajian simulasi mendapati bahawa pencapaian peranti ini tidak mempunyai kelebihan yang nyata berbanding MOSFET dan pencapaian peranti ini juga dipengaruhi oleh diameter tiub-nano karbon serta ketebalan oksida.

TABLE OF CONTENTS

CHAPTER	TITLE	PAGE
	TITLE PAGE	i
	DECLARATION	ii
	DEDICATION	iii
	ACKNOWLEDGEMENTS	iv
	ABSTRACT	v
	ABSTRAK	vi
	TABLE OF CONTENTS	vii
	LIST OF TABLES	x
	LIST OF FIGURES	xi
	LIST OF SYMBOLS	xv
	LIST OF APPENDICES	xvii
1	INTRODUCTION	
	1.1 Project objectives	1
	1.2 Scope of project	2
	1.3 Layout of thesis	2
2	OVERVIEW OF MOSFET AND NANOELECTRONIC DEVICES	
	2.1 MOSFET: Gateway to nanoelectronic devices	4
	2.2 Limitations to MOSFET scaling	7
	2.2.1 Short channel effect	7
	2.2.2 Tunnelling effect	9

2.2.3	Ballistic transport	9
2.2.4	Threshold voltage	10
2.2.5	Oxide thickness	11
2.2.6	Theoretical limit	12
2.2.7	Technology limit	13
2.2.8	Economy limit	13
2.3	Introduction to nanoelectronic devices	14
2.3.1	Single-electron transistors	14
2.3.2	Resonant tunnelling devices	17
2.3.3	Carbon nanotube field-effect transistor (CNFET)	22
2.3.4	Sub-10nm MOSFET	23
2.4	Summary	25

3 CARBON NANOTUBE STRUCTURES, PROPERTIES AND GROWTH

3.1	Background	26
3.2	Structure of Carbon Nanotube	27
3.2.1	Single-Walled Carbon Nanotube	27
3.2.2	Multi-Walled Carbon Nanotube	29
3.3	Properties of Carbon Nanotube	30
3.3.1	Electron transport in SWNT	33
3.3.2	Electron transport of MWNT	34
3.4	Growth of Carbon Nanotube	34
3.4.1	Chemical Vapour Deposition	35
3.4.2	Arc Discharge	37
3.4.3	Laser Ablation	38
3.4.4	Gas-phase Catalytic	38
3.5	Carbon Nanotube Applications	39
3.5.1	Electronic device	39
3.5.2	Chemical and Physical Sensors	40
3.6	Summary	45

4	CARBON NANOTUBE FIELD EFFECT TRANSISTOR	
4.1	Structure of CNFET	47
	4.1.1 Back-gated CNFET	47
	4.1.2 Top-gated CNFET	49
	4.1.3 Vertical CNFET	50
4.2	Operation of CNFET	51
	4.2.1 Schottky-barrier CNFET	52
	4.2.2 MOSFET-like CNFET	53
4.3	P-type versus N-type CNFET	54
4.4	Application of CNFET	56
4.5	Summary	59
5	RESULT AND ANALYSIS	
5.1	Methodology	61
5.2	Result	65
5.3	Analysis	67
	5.3.1 Comparison with MOSFET	67
	5.3.2 Effect of gate oxide thickness on drain current	68
	5.3.3 Effect of CNT diameter on drain current	73
5.4	Discussion	79
5.5	Summary	80
6	CONCLUSION AND FUTURE WORK	
6.1	Conclusion	81
6.2	Future work	83
	REFERENCES	84
	APPENDIX A	88
	APPWNDIX B	92

LIST OF TABLES

TABLE NO.	TITLE	PAGE
3.1	Classification of carbon nanotube.	28
3.2	Important electrical and mechanical properties of CNT.	31
5.1	Drain current corresponding to gate oxide thickness.	74
5.2	Drain current corresponding to CNT diameter.	78

LIST OF FIGURES

FIGURE NO.	TITLE	PAGE
2.1	Structure of MOSFET.	5
2.2	(a) MOSFET at OFF state, (b) MOSFET at ON state.	5
2.3	Semiconductor technology minimum feature size trend	6
2.4	Intel CPU transistor count trend.	6
2.5	Short-channel-transistor leakage current mechanisms.	8
2.6	Potential barrier between two transistors.	9
2.7	Ballistic transport in transistor channel.	10
2.8	Measured and calculated oxide tunnelling current vs. gate voltage for different oxide thickness.	11
2.9	Trends of threshold voltage and gate oxide thickness vs. channel length for CMOS technology.	12
2.10	Tunnel junction and its schematic diagram.	15
2.11	Circuit for single-electron transistor (SET).	15
2.12	Energy band diagram when (a) Coulomb blockade and (b) tunnelling.	16
2.13	Structure of Resonant Tunnelling Diode (RTD).	17
2.14	(a) Schematic diagram of RTD structure,(b) RTD in OFF state, (c) RTD is in ON state.	18
2.15	I-V characteristic of RTD.	19
2.16	(a) Schematic of RTD latch, (b) load-line diagram.	20
2.17	(a) Delay, (b) OR gate, (c) XOR gate (also NOT) (d) AND gate.	21
2.18	(a) RTD shift register schematic diagram, (b) simplified overlapping clock waveform.	21
2.19	Double-gate SBFET with silicide/metal source and drain.	23

2.20	Cross section of CNFET.	24
2.21	CNT structure.	24
3.1	Three types of single-walled carbon nanotube.	28
3.2	The graphite sheet of a nanotube showing state vectors \mathbf{a}_1 and \mathbf{a}_2 and axis vector T about sheet is rolled.	28
3.3	Structure of multi-walled carbon nanotube.	29
3.4	Current induced electrical breakdown process in multi-walled carbon nanotube.	30
3.5	Different rolling direction and resulting electrical conduction type.	32
3.6	Metallic SWNT has armchair structure and semiconducting has zigzag structure.	32
3.7	Typical device geometry for electrical transport measurement.	34
3.8	Schematic setup for chemical vapour deposition.	35
3.9	Top and side view of grown CNT.	36
3.10	The process step to produce SWNT by CVD process using methane as source of carbon.	36
3.11	Apparatus for arc-discharge.	37
3.12	Single-walled carbon nanotube produced by laser ablation.	38
3.13	CNT-based field-effect transistor.	40
3.14	Category of CNT-based chemical sensors.	40
3.15	Equivalent circuit of chemiresistors.	41
3.16	Structure of CNT-based resonator.	42
3.17	Equivalent circuit model to describe electrical characteristic of resonator with no load condition.	42
3.18	Structure of CNT-based flow sensor.	43
3.19	Charge injection on CNT-based electromechanical structure.	44
3.20	Basic cell of CNT-based IR detector.	44
4.1	Image of back-gated CNFET.	48
4.2	Schematic cross section of back-gated CNFET.	48
4.3	Top-gated structure of CNFET.	49
4.4	Device structure of vertical CNFET.	50

4.5	Another view of vertical CNFET.	51
4.6	Diagram of Schottky-barrier CNFET (SB-CNFET).	52
4.7	Diagram of MOSFET-like CNFET.	53
4.8	Characteristic of CNFET due to annealing process.	55
4.9	CNFET characteristic due to exposure to potassium atom.	56
4.10	Schematic diagram of intermolecular logic gate.	57
4.11	AFM image of intramolecular logic gate.	57
4.12	Schematic of CNFET-based NOT gate.	59
4.13	Schematic of CNFET-based NOR gate.	59
5.1	The simulation model for ballistic CNFET.	62
5.2	Flow chart of simulation process.	64
5.3	Flow chart of simulation process in MATLAB program.	65
5.4	Structure of simulated ballistic CNFET	66
5.5	Plot of I_D vs. V_D .	66
5.6	Plot of I_D vs. V_G .	67
5.7	I_D vs. V_D for sub-10nm MOSFET.	68
5.8	I_D vs. V_G for sub-10nm MOSFET.	69
5.9	Simulated ballistic CNFET with 1nm diameter and varying gate oxide thickness.	69
5.10	Plot of I_D vs. V_D for CNT diameter 1.0nm and gate oxide thickness 0.5nm.	70
5.11	Plot of I_D vs. V_G for CNT diameter 1.0nm and gate oxide thickness 0.5nm.	70
5.12	Plot of I_D vs. V_D for CNT diameter 1.0nm and gate oxide thickness 1.0nm.	71
5.13	Plot of I_D vs. V_G for CNT diameter 1.0nm and gate oxide thickness 1.0nm.	71
5.14	Plot of I_D vs. V_D for CNT diameter 1.0nm and gate oxide thickness 2.0nm.	72
5.15	Plot of I_D vs. V_G for CNT diameter 1.0nm and gate oxide thickness 2.0nm.	72
5.16	Plot of I_D vs. V_D for CNT diameter 1.0nm and gate oxide thickness 2.5nm.	73
5.17	Plot of I_D vs. V_G for CNT diameter 1.0nm and gate	

	oxide thickness 2.5nm.	73
5.18	Simulated ballistic CNFET with 1.5nm gate oxide thickness and varying nanotube diameter	75
5.19	Plot of I_D vs. V_D for CNT diameter 0.5nm and gate oxide thickness 1.5nm.	75
5.20	Plot of I_D vs. V_G for CNT diameter 0.5nm and gate oxide thickness 1.5nm.	76
5.21	Plot of I_D vs. V_D for CNT diameter 1.5nm and gate oxide thickness 1.5nm.	76
5.22	Plot of I_D vs. V_G for CNT diameter 1.5nm and gate oxide thickness 1.5nm.	77
5.23	Plot of I_D vs. V_D for CNT diameter 2.0nm and gate oxide thickness 1.5nm.	77
5.24	Plot of I_D vs. V_G for CNT diameter 2.0nm and gate oxide thickness 1.5nm.	78

LIST OF SYMBOLS

α_D	-	Coefficient of drain capacitance
α_G	-	Coefficient of gate capacitance
α_S	-	Coefficient of source capacitance
C_D	-	Drain terminal capacitance
C_G	-	Gate terminal capacitance
C_S	-	Source terminal capacitance
C_Σ	-	Total capacitance
$D(E)$	-	Carbon nanotube density of states at top of the barrier
E_{F1}	-	Source Fermi level (eV)
E_{F2}	-	Drain Fermi level (eV)
$f(E)$	-	Probability that a state with energy E is occupied
h	-	Planck's constant (eV-s)
I_0	-	Extrapolated current per width at threshold voltage
I_D	-	Drain current (I)
I_{ON}	-	On-current
I_{OFF}	-	Leakage current
k_B	-	Boltzmann's constant (eV/K)
m	-	Gate voltage swing required per unit of electron potential
N_0	-	Equilibrium electron density at top of the barrier
N_1	-	Positive velocity states filled by source
N_2	-	Negative velocity states filled by drain
q	-	Electronic charge (C)
T	-	Operating temperature (K)
U_L	-	Laplace potential
U_P	-	Potential due to mobile charge
U_{scf}	-	Self-consistent potential at top of the barrier
V_D	-	Drain voltage (V)

V_G	-	Gate voltage (V)
V_S	-	Source voltage (V)
V_t	-	Threshold voltage (V)

LIST OF APPENDICES

APPENDIX	TITLE	PAGE
A	MATLAB Source Code for Ballistic CNFET Simulation	88
B	Mathematical Derivation for Ballistic CNFET Simulation	92

CHAPTER 1

INTRODUCTION

As an introduction, this chapter presents the objectives and scopes of this project and background of this project. This chapter also gives outline of this thesis as well as summary of content for each chapter.

1.1 Project Objectives

The main interest of this project is to study the characteristic one nanoelectronic device. Ballistic carbon nanotube field-effect transistor (CNFET) is chosen as one of nanoelectronic devices that have great potential to be the switching device for future. The main objectives of this project are as follows:

- a) Understand the device characteristic, fundamental equation and mathematical model of CNFET.
- b) To attain and investigate the I-V characteristics of CNFET.

The means through which the main objectives could be achieved are:

- a) To study the behaviour of carbon nanotube, the most important material that is used to build CNFET.
- b) Identify the most suitable structure of CNFET that can promote ballistic transport.

1.2 Scope of Project

The scope of this project is to carry out simulation study of carbon nanotube field-effect transistor using MATLAB program based on the mathematical model. The structure of MOSFET-like CNFET is used in this project because this structure has better performance than Schottky-barrier CNFET (SB-CNFET). The simulation result is then compared with MOSFET in order to measure the level of CNFET performance.

1.3 Layout of Thesis

This thesis consists of six chapters beginning with this chapter. Chapter 1 gives the objectives and scope of the project as well as the layout of thesis.

Chapter 2 presents an overview of nanoelectronic devices such as single electron transistors, resonant tunnelling diode and carbon nanotube field-effect transistor. This chapter also discussed the limiting factors that prevent improvement in MOSFET performance as its size is kept on shrinking.

Chapter 3 is dedicated to carbon nanotube, the material used as transistor channel in CNFET. This chapter discussed the background of carbon nanotube, its basic structure as well as its properties that make it very special material. Growth technique of this material is presented briefly to give an overview of how this material is produced.

Chapter 4 deals with CNFET, the basis of research in this project. It starts with its structure, followed by simple explanation on its operation and finally the applications associated with this device.

Chapter 5 presents the simulation result of this project. This result is then analysed through comparison with MOSFET and also factors that affects the performance of CNFET.

Finally, Chapter 6 gives conclusion for the whole project. This chapter also presents several recommendations for future work.

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